

# **RE46C145**

# CMOS Photoelectric Smoke Detector ASIC with Interconnect and Timer Mode

#### Features:

- · Internal Power On Reset
- · Low Quiescent Current Consumption
- · ESD Protection on all Pins
- Interconnect up to 40 Detectors
- · 10 Minute Timer for Sensitivity Control
- · Temporal Horn Pattern
- · Internal Low Battery and Chamber Test
- · Compatible with Allegro A5366
- · Alternate Diagnostic Mode
- · UL Recognized per File S24036

# **General Description:**

The RE46C145 is a low-power, CMOS photoelectric-type smoke detector IC. With minimal external components, this circuit will provide all the required features for a photoelectric-type smoke detector.

The design incorporates a gain-selectable photo amplifier for use with an infrared emitter/detector pair.

An internal oscillator strobes power to the smoke detection circuitry for 100  $\mu$ s every 10 seconds to keep standby current to a minimum. If smoke is sensed, the detection rate is increased to verify an Alarm condition. A High Gain mode is available for push button chamber testing.

In diagnostic mode, the photo amplifier output is available on pin 15 for production calibration of the photo chamber.

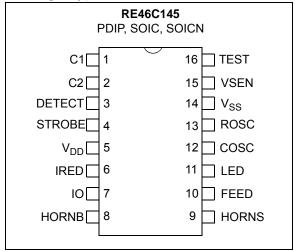
When in Standby, a check for a low battery condition and chamber integrity is performed every 43 seconds. The temporal horn pattern supports the NFPA 72 emergency evacuation signal.

An interconnect pin allows multiple detectors to be connected such that when one units alarms, all units will sound.

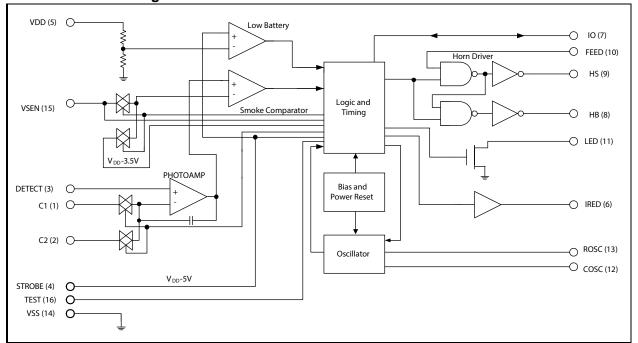
An internal 10 minute timer can be used for a reduced sensitivity mode.

The RE46C145 is recognized by Underwriters Laboratories for use in smoke detectors that comply with specification UL217 and UL268.

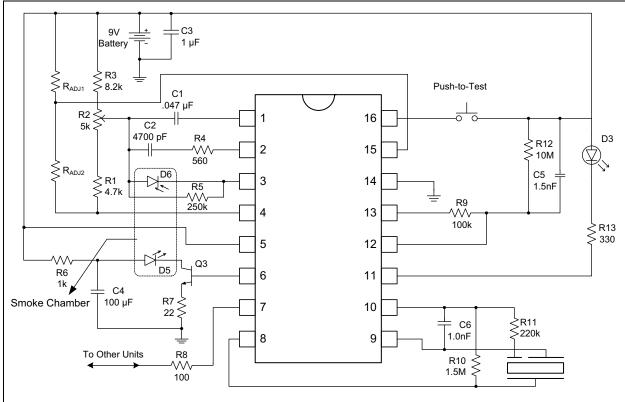
# Package Types



# **Functional Block Diagram**



# **Typical Application**



- Note 1: C3 should be located as close as possible to the device power pins.
  - 2: C3 is typical for an alkaline battery. This capacitance should be increased to 4.7 µF or greater for a carbon battery.
  - 3: R10, R11 and C6 are typical values and may be adjusted to maximize sound pressure.

# 1.0 ELECTRICAL CHARACTERISTICS

# 1.1 Absolute Maximum Ratings†

V <sub>DD</sub>	15V
Input Voltage Range Except FEED, IO	$V_{IN}$ =3V to $V_{DD}$ +.3V
FEED Input Voltage Range	V <sub>INFD</sub> =-10 to +22V
IO Input Voltage Range	V <sub>IO1</sub> =3 to 15V
Input Current except FEED	I <sub>IN</sub> = 10 mA
Operating Temperature	$T_{A} = -25 \text{ to } +75^{\circ}\text{C}$
Storage Temperature	$T_{STG} = -55 \text{ to } +125^{\circ}\text{C}$
Maximum Junction Temperature	T <sub>.l</sub> = +150°C

† Notice: Stresses above those listed under "Maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

DC Electrical Charact	teristics: Unle	ss otherw	ise indicat	ed, all pa	rameters ar	oply at 1	$\Gamma_{A} = -25^{\circ}\text{C to } +75^{\circ}\text{C}, V_{DD} = 9\text{V}$
Parameter	Symbol	Test Pin	Min	Тур	Max	Units	Conditions
Supply Voltage	$V_{DD}$	5	6	_	12	V	Operating
Supply Current	I <sub>DD1</sub>	5	_	4	6	μA	Configured as in Typical Application, COSC = V <sub>SS</sub> , LED off
	I <sub>DD2</sub>	5	_	5.5	8	μA	Configured as in Typical Application, V <sub>DD</sub> = 12V, COSC = V <sub>SS</sub>
	I <sub>DD3</sub>	5	_	_	2	mA	Configured as in Typical Application, STROBE on, IRED off, V <sub>DD</sub> =12V
	I <sub>DD4</sub>	5	_	_	3	mA	Configured as in Typical Application, STROBE on, IRED on, V <sub>DD</sub> = 12V, <b>Note 1</b>
Input Voltage High	V <sub>IH1</sub>	10	6.2	_	_	V	FEED
	V <sub>IH2</sub>	7	3.2	_	_	V	No Local Alarm, IO as Input
	V <sub>IH3</sub>	15	1.6	_	_	V	V <sub>SEN</sub>
	V <sub>IH4</sub>	16	8.5	_	_	V	TEST
Input Voltage Low	V <sub>IL1</sub>	10	_	_	2.7	V	FEED
	V <sub>IL2</sub>	7	_	_	1.5	V	No Local Alarm, IO as Input
	V <sub>IL3</sub>	15	_	_	.5	V	V <sub>SEN</sub>
	V <sub>IL4</sub>	16	_	_	7	V	TEST
Input Leakage Low	I <sub>IL1</sub>	1,2,3	_	_	-100	nA	V <sub>DD</sub> = 12V, COSC = 12V, STROBE active
	I <sub>IL2</sub>	10,12	_		-100	nA	$V_{DD}$ = 12V, $V_{IN}$ = $V_{SS}$
	I <sub>IL3</sub>	15,16	_	_	-1	μA	$V_{DD}$ = 12V, $V_{IN}$ = $V_{SS}$
	I <sub>LFD</sub>	10	_	_	-50	μA	FEED = -10V

- Note 1: Does not include Q3 emitter current.
  - 2: Not production tested.
  - **3:** Typical values are for design information and are not ensured.
  - **4:** Limits over the specified temperature range are not production tested and are based on characterization data.

# DC ELECTRICAL CHARACTERISTICS (CONTINUED)

DC Electrical Character	istics: Unle	ss otherw	ise indicat	ed, all pa	rameters ap	ply at 1	$T_A = -25^{\circ}\text{C to } +75^{\circ}\text{C}, V_{DD} = 9\text{V}$
Parameter	Symbol	Test Pin	Min	Тур	Max	Units	Conditions
Input Leakage High	I <sub>IH1</sub>	1,2	_	_	100	nA	$V_{DD}$ = 12V, $V_{IN}$ = $V_{DD}$ , STROBE active
	I <sub>IH2</sub>	3,10,12	_		100	nA	$V_{DD}$ = 12V, $V_{IN}$ = $V_{DD}$
	I <sub>HFD</sub>	10	_		50	μΑ	FEED = 22V
Input Pull Down Current	I <sub>PD1</sub>	16	.25		10	μΑ	$V_{IN} = V_{DD}$
	I <sub>PD2</sub>	15	.1	.25	.5	μΑ	$V_{IN} = V_{DD}$
	I <sub>PDIO1</sub>	7	20		80	μΑ	$V_{IN} = V_{DD}$
	I <sub>PDIO2</sub>	7	_	_	140	μΑ	V <sub>IN</sub> = 15V, V <sub>DD</sub> = 12
Output Leakage Current Low	I <sub>OZL1</sub>	11,13	_	_	-1	μΑ	Output Off, Output = V <sub>SS</sub>
Output Leakage Current High	I <sub>OZH1</sub>	11,13	_	_	1	μΑ	Output Off, Output = V <sub>DD</sub>
Output Voltage Low	V <sub>OL1</sub>	8,9	_		1	٧	IoI = 16 mA, V <sub>DD</sub> = 6.5V
	$V_{OL2}$	13		.5	_	٧	$IoI = 5 \text{ mA}, V_{DD} = 6.5 \text{V}$
	$V_{OL3}$	11			.6	<b>V</b>	$IoI = 10 \text{ mA}, V_{DD} = 6.5V$
Output Voltage High	V <sub>OH1</sub>	8,9	5.5			>	IoI = -16 mA, V <sub>DD</sub> = 6.5V
Output Current	I <sub>IOH1</sub>	7	-4	_	-16	mA	Alarm, $V_{IO} = V_{DD}$ –2V or $V_{IO} = 0V$
	I <sub>IODMP</sub>	7	5	_	_	mA	At Conclusion of Local Alarm or Test, VV <sub>IO</sub> = 1V
Low Battery Alarm Voltage	$V_{LB}$	5	6.9	7.2	7.5	V	
Output Voltage	V <sub>STOF</sub>	4	V <sub>DD</sub> 1	_	_	V	STROBE off, $V_{DD} = 12V$ , $I_{OUT} = -1 \mu A$
	V <sub>STON</sub>	4	V <sub>DD</sub> - 5.25	V <sub>DD</sub> –5	V <sub>DD</sub> -4.75	>	STROBE on, $V_{DD}$ = 9V $I_{OUT}$ = 100 $\mu$ A to 500 $\mu$ A
	V <sub>IREDOF</sub>	6			.1	<b>V</b>	IRED off, $V_{DD}$ = 12V, $I_{OUT}$ = 1 $\mu$ A
	V <sub>IREDON</sub>	6	2.85	3.1	3.35	V	IRED on, $V_{DD} = 9V$ $I_{OUT} = 0$ to -6 mA, $T_A = +25$ °C
Common Mode Voltage	V <sub>CM1</sub>	1,2,3	.5	_	V <sub>DD</sub> –2	V	Local smoke, Push to Test or Chamber Test, Note 2
Smoke Comparator Reference	V <sub>REF</sub>	-	V <sub>DD</sub> -3.7		V <sub>DD</sub> -3.3	<b>V</b>	Internal Reference
Temperature Coefficient	T <sub>CST</sub>	4	_	.01	_	%/°C	V <sub>DD</sub> = 6V to 12V, STROBE Output Voltage
	T <sub>CIRED</sub>	6	_	.3	_	%/°C	V <sub>DD</sub> = 6V to 12V, IRED Output Voltage
Line Regulation	$\Delta V_{STON}$	4,5	_	-50	_	dB	Active, V <sub>DD</sub> =6V to 12V
	$\Delta V_{IREDON}$	6,5	_	-30	_	dB	Active, V <sub>DD</sub> = 6V to 12V

Note 1: Does not include Q3 emitter current.

<sup>2:</sup> Not production tested.

**<sup>3:</sup>** Typical values are for design information and are not ensured.

**<sup>4:</sup>** Limits over the specified temperature range are not production tested and are based on characterization data.

# **AC ELECTRICAL CHARACTERISTICS**

**AC Electrical Characteristics:** Unless otherwise indicated, all parameters apply at  $T_A$  = -25°C to +75°C,  $V_{DD}$  = 9V,  $V_{SS}$  = 0V, Component Values from Typical Application;  $R_9$  = 100 K $\Omega$ ,  $R_{12}$  = 10 M $\Omega$ ,  $R_{5}$  = 1.5 nF

Parameter	Symbol	Test Pin	Min	Тур	Max	Units	Test Conditions
Oscillator Period	T <sub>POSC</sub>	12	9.4	10.5	11.5	ms	No alarm condition
LED and STROBE On Time	T <sub>ON1</sub>	11,4	9.4	10.5	11.5	ms	Operating
LED Period	T <sub>PLED1</sub>	11	39	43	47	S	Standby, no alarm
	T <sub>PLED2</sub>	11	.45	.5	.55	S	Local alarm condition
	T <sub>PLED3</sub>	11	9.6	10.75	11.8	s	Timer mode, no local alarm
	$T_{PLED4}$	11	LE	D IS NOT	ON	S	Remote alarm only
STROBE	T <sub>PER1</sub>	4,6	9.6	10.75	11.8	S	Standby, no alarm
and IRED Pulse Period	T <sub>PER1A</sub>	4,6	1.8	2	2.2	s	Standby, after one valid smoke sample
	T <sub>PER1B</sub>	4,6	.9	1	1.1	s	Standby, after two consecutive valid smoke samples
	T <sub>PER2</sub>	4,6	.9	1	1.1	S	In Local Alarm (three consecutive valid smoke samples)
	T <sub>PER3</sub>	4,6	7.2	8	8.9	S	In Remote Alarm
	T <sub>PER4</sub>	4,6	300	336	370	ms	Push-button test
	T <sub>PER5</sub>	4,6	39		47	s	Chamber Test or Low Battery Test, no alarms
IRED On Time	T <sub>ON2</sub>	6	94	104	115	μs	Operating
Horn On Time	T <sub>HON1</sub>	8,9	450	500	550	ms	Operating, alarm condition, Note 1
	T <sub>HON2</sub>	8,9	9.5	10.5	11.5	ms	Low Battery or Failed Chamber test, no alarm
Horn Off Time	T <sub>HOF1</sub>	8,9	450	500	550	ms	Operating, alarm condition, Note 1
	T <sub>HOF2</sub>	8,9	1.35	1.5	1.65	S	Operating, alarm condition, Note 1
	T <sub>HOF3</sub>	8,9	39	43	47	s	Low Battery or Failed Chamber test, no alarm
IO Charge Dump Duration	$T_IODMP$	7	.9		1.46	s	At the conclusion of the Local Alarm or Test
IO Delay	T <sub>IODLY1</sub>	7		0		s	From start of Local Alarm to IO Active
IO Filter	T <sub>IOFILT</sub>	7			600	mSs	IO pulse-width ensured to be filtered. IO as input, no local alarm
Remote Alarm Delay	T <sub>IODLY2</sub>	7	1.05		2.0	S	No local alarm, from IO Active to Horn Active
Timer Period	T <sub>TPER</sub>		7	8.5	10	Min	No alarm condition, Note 2

- Note 1: See timing diagram for Horn Temporal Pattern
  - 2: During the Timer mode, the LED period is 10.5 seconds. The LED period will return to 43 seconds at the conclusion of the Timer mode.
  - 3: T<sub>POSC</sub> and T<sub>ON2</sub> are 100% production tested. All other timing is ensured by functional testing.
  - **4:** Typical values are for design information and are not ensured.

# **RE46C145**

# **TEMPERATURE CHARACTERISTICS**

Electrical Specifications: Unless otherwise indicated, V <sub>DD</sub> = 9V, V <sub>SS</sub> = 0V							
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions	
Temperature Ranges							
Operating Temperature Range	T <sub>A</sub>	-25	_	+75	°C		
Storage Temperature Range	T <sub>STG</sub>	-55	_	+125	°C		
Thermal Package Resistances							
Thermal Resistance, 16L-PDIP	θJ <sub>A</sub>	_	70	_	°C/W		
Thermal Resistance, 16L-SOIC (150 mil.)	θJ <sub>A</sub>	_	86.1	_	°C/W		
Thermal Resistance, 16L-SOIC (300 mil.)	θJ <sub>A</sub>	_	80	_	°C/W		

#### 2.0 PIN DESCRIPTION

The descriptions of the pins are listed in .

TABLE 2-1: PIN FUNCTION TABLE

RE46C145 PDIP, SOIC, SOICN	Symbol	Function
1	C1	High Gain Capacitor Pin
2	C2	Normal Gain Capacitor Pin
3	DETECT	Photo Diode Input
4	STROBE	Strobed Detection Negative Supply
5	$V_{DD}$	Positive Power Supply
6	IRED	Infrared Emitting Diode Pin
7	Ю	Interconnect Pin
8	HB	Horn Brass, Inverted Output
9	HS	Horn Silver Output
10	FEED	Horn Feedback Pin
11	LED	LED Driver Pin
12	COSC	Oscillator Capacitor Input
13	ROSC	Oscillator Resistor Drive Low
14	V <sub>SS</sub>	Negative Power Supply
15	VSEN	HushTimer Sensitivity Pin
16	TEST	Test Pin

# 2.1 High/Normal Gain Capacitor Pins (C1, C2)

The capacitor connected to C1 pin sets the photo amplifier gain (high) for the push-to-test and chamber sensitivity test. The size of this capacitor will depend on the chamber background reflections. A = 1+(C1/10), where C1 is expressed in pF. The gain should be <10000.

The capacitor connected to C2 pin sets the photo amplifier gain (normal) during standby. The value of this capacitor will depend on the smoke sensitivity required. A = 1+(C2/10), where C2 is expressed in pF.

# 2.2 Photo Diode Input (DETECT)

This input is normally connected to the cathode of an external photo diode operated at zero bias.

# 2.3 Strobed Detection Negative Supply (STROBE)

Regulated output voltage of  $V_{DD}$ -5 which is active during a test for smoke. This output is the negative side of the photo amplifier reference circuitry.

# 2.4 Positive Power Supply (V<sub>DD</sub>)

The V<sub>DD</sub> pin is the device's positive power supply input.

# 2.5 Infrared Emitting Diode Pin (IRED)

Provides a regulated pulsed output voltage pre-driver for the infrared emitter. This output usually drives the base of an NPN transistor.

# 2.6 Interconnect Pin (IO)

This bidirectional pin provides the capability to interconnect many detectors in a single system. This pin has an internal pull-down device.

#### 2.7 Horn Brass, Inverted Output (HB)

HB pin is connected to the metal electrode of a piezoelectric transducer.

# 2.8 Horn Silver Output Pin (HS)

HS pin is a complementary output to HB and connects to the ceramic electrode of the piezoelectric transducer.

# **RE46C145**

# 2.9 Horn Feedback Pin (FEED)

Usually this pin is connected to the feedback electrode through a current limiting resistor. If not used, this pin must be connected to  $V_{DD}$  or  $V_{SS}$ .

# 2.10 LED Driver Pin (LED)

This pin is an open drain NMOS output used to drive a visible LED.

# 2.11 Oscillator Capacitor Input (COSC)

A capacitor connected to this pin, with a parallel resistor, sets the internal clock low time, which is approximately the clock period.

# 2.12 Oscillator Resistor Drive Low (ROSC)

A resistor between this pin and COSC pin sets the internal clock high time. This also sets the IRED pulse width (100 - 200  $\mu$ s).

## 2.13 Hush Timer Sensitivity Pin (VSEN)

In Timer mode, this input pin can be used to set an external smoke comparator reference.

# 2.14 TEST Pin

This input is used to invoke two test modes and the Timer mode. This input has an internal pull-down.

#### 3.0 DEVICE DESCRIPTION

Note: All timing references are nominal. See Electrical Characteristics for limits.

# 3.1 Standby Internal Timing

With the external components specified in the Typical Application for R12 and C5, the internal oscillator has a nominal period of 10 ms. Normally the analog circuitry is powered down to minimize standby current (typically 4  $\mu A$  at 9V). Once every 10 seconds the detection circuitry (normal gain) is powered up for 10 ms. Prior to completion of the 10 ms period, the IRED pulse is active for 100  $\mu s$ . At the conclusion of the 10 ms period, the photo amplifier is compared to an internal reference to determine the chamber status and latched. If a smoke condition is present, the period to the next detection decreases and additional checks are made. Three consecutive smoke detections will cause the device to go into alarm, and the horn circuit and interconnect will be active.

Once every 43 seconds the status of the battery voltage is checked. This status is checked and latched at the conclusion of the LED pulse. In addition, once every 43 seconds the chamber is activated and, using the high gain mode (capacitor C1), a check of the chamber is made by amplifying background reflections. If either the low battery or the photo chamber test fails, the horn will chirp for 10 ms every 43 seconds.

The oscillator period is determined by the values of R9, R12 and C5 (see Typical Application). The oscillator period is as follows:

#### **EQUATION 3-1:**

$$T = T_R + T_F$$
  
Where:  
 $T_R = .6931 \times R12 \times C5$   
 $T_F = .6931 \times R9 \times C5$ 

# 3.2 Smoke Detection Circuitry

A comparator compares the photo amp output to an internal reference voltage. If the required number of consecutive smoke conditions is met, the device will go into local alarm and the horn will be active. In local alarm, the C2 gain is internally increased by approximately 10% to provide alarm hysteresis.

#### 3.3 Push-to-Test Operation

If the TEST input pin is activated ( $V_{IH}$ ), after one internal clock cycle, the smoke detection rate increases to once every 330 ms. In this mode, the high-gain capacitor C1 is selected, and background reflections are used to simulate a smoke condition. After the required consecutive detections, the device will go into a local alarm condition. When the TEST input is deactivated ( $V_{IL}$ ) and after one clock cycle, the normal gain capacitor C1 is selected. The detection rate continues at once every 330 ms until three consecutive no smoke conditions are detected. At this point, the device returns to standby timing.

#### 3.4 LED Operation

In standby, the LED is pulsed on for 10 ms every 43 seconds. In a local alarm condition or the push-to-test alarm, the LED pulse frequency is increased to once every .5 seconds. In the case of a remote alarm, the LED is not active. In the Timer mode of operation, the LED is pulsed on for 10 ms every 10 seconds.

## 3.5 Interconnect Operation

The bidirectional I/O pin allows for interconnection of multiple detectors. In a local alarm condition, this pin is driven high immediately through a constant current source. Shorting this output to ground will not cause excessive current. The I/O is ignored as an input during a local alarm.

The I/O pin also has an NMOS discharge device that is active for 1 second after the conclusion of any type of local alarm. This device helps to quickly discharge any capacitance associated with the interconnect line.

If a remote active-high signal is detected, the device goes into remote alarm and the horn will be active. Internal protection circuitry allows for the signaling unit to have a higher supply voltage than the signaled unit, without excessive current draw.

The interconnect input has a 670 ms nominal digital filter. This allows for interconnection to other types of alarms (carbon monoxide, for example) that may have a pulsed interconnect signal.

#### 3.6 Low Battery Detection

In standby, an internal reference is compared to the voltage divided  $V_{DD}$  supply. A low battery status is latched at the conclusion of the LED pulse. The horn will chirp for 10 ms every 43 seconds, until the low battery condition no longer exists. The low battery test is not performed in a local or remote alarm condition.

The low battery notification does not sound in a local or remote alarm condition.

#### 3.7 Chamber Fail Detection

In standby, a chamber test is also performed every 43 seconds, by switching to the high gain capacitor C1 and sensing the photo chamber background reflections. Two consecutive chamber test failures will also cause the horn to chirp for 10 ms every 43 seconds. The low battery chirp occurs just before the LED pulse (see Figure 3-1). The chamber test and chamber test failure chirp occurs approximately 21 seconds after the LED pulse. The chamber tests are not performed in a local or remote alarm condition.

The chamber fail notification does not sound in a local or remote alarm condition.

#### 3.8 Timer Mode

If resistors  $R_{ADJ1}$  and  $R_{ADJ2}$  are in place and a high-to-low transition occurs on the TEST input, the device enters a 10 minute timer mode. In this mode, the smoke comparator reference is switched from the internal  $V_{DD}$  - 3.5V reference to the voltage that appears on VSEN (pin 15). This allows the sensitivity to be modified for the duration of the 9 minute timer period. The chamber test is performed in Timer mode.

If VSEN is left unconnected or tied to  $V_{SS}$ , the Timer mode of operation is inhibited.

# 3.9 Diagnostic Mode

In addition to the normal function of the TEST input, a special diagnostic mode is available to calibrate and test of the smoke detector. Taking the TEST pin below  $V_{SS}$  and sourcing ~200  $\mu A$  out of the pin for 1 clock cycle will enable the diagnostic mode. In the diagnostic mode, some of the pin functions are redefined. Refer to Table 3-1 for redefined pin functions in the diagnostic mode. In addition, in this mode STROBE is always enabled, and the IRED is pulsed at the clock rate of 10 ms nominal.

TABLE 3-1: DIAGNOSTIC MODE PIN FUNCTION

Pin Name	Pin Number	Function
Ю	7	The IO pin (7) controls the gain capacitor used for the photo amplifier. If IO is low, then normal gain is selected. If IO is high, then high gain is selected.
VSEN	15	In Diagnostic mode, the output of the photo amplifier is gated to this pin and the pull-down device is disabled
FEED	10	If the IO pin (7) is low, then taking this input high will enable hysteresis, which is a nominal 10% gain increase in Normal Gain mode.
COSC	12	If desired, this pin can be driven by an external clock.
HORNB	8	This pin becomes the smoke integrator output. A high level indicates that an alarm condition has been detected.
LED	11	The LED pin is used as a low battery indicator. For $V_{DD}$ above the low battery threshold, the open drain NMOS is off. If $V_{DD}$ falls below the threshold, the NMOS turns on.

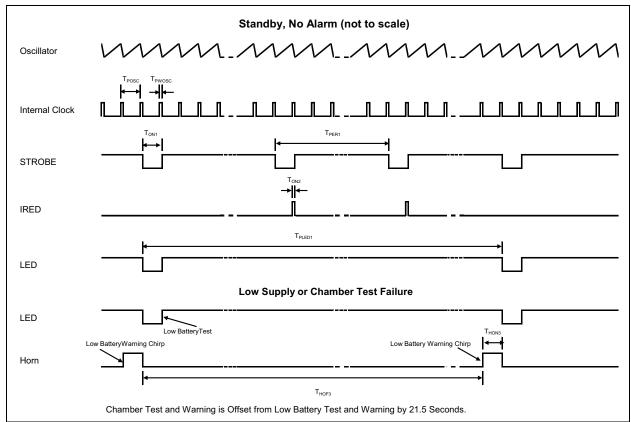


FIGURE 3-1: RE46C145 Timing Diagram – Standby, Low Supply and Chamber Test Failure.

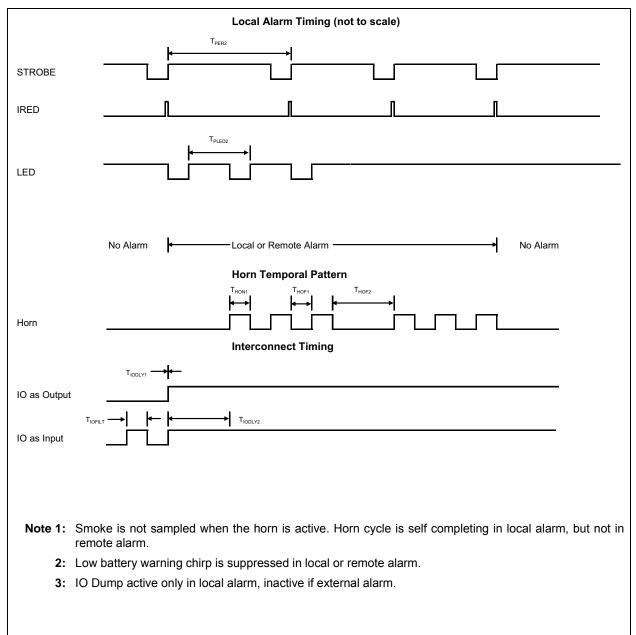
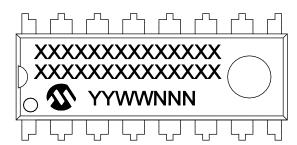


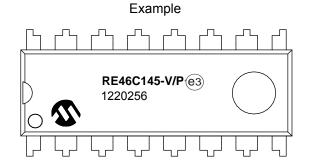
FIGURE 3-2: RE46C145 Timing Diagram – Local Alarm, Horn and Interconnect Timings.

#### 4.0 PACKAGING INFORMATION

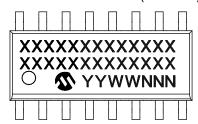
# 4.1 Package Marking Information

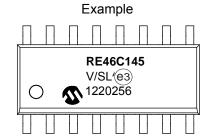
16-Lead PDIP (300 mil)



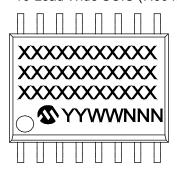


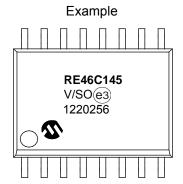
16-Lead Narrow SOIC (3.90 mm)





16-Lead Wide SOIC (7.50 mm)





Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

(e3) Pb-free JEDEC designator for Matte Tin (Sn)

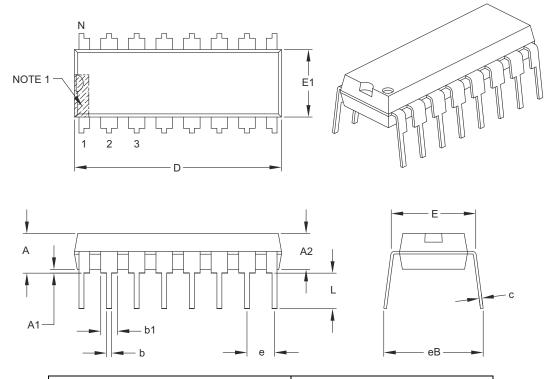
This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

# 16-Lead Plastic Dual In-Line (P) - 300 mil Body [PDIP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		INCHES	
	Dimension Limits	MIN	NOM	MAX
Number of Pins	N		16	
Pitch	е		.100 BSC	
Top to Seating Plane	A	_	_	.210
Molded Package Thickness	A2	.115	.130	.195
Base to Seating Plane	A1	.015	_	_
Shoulder to Shoulder Width	E	.290	.310	.325
Molded Package Width	E1	.240	.250	.280
Overall Length	D	.735	.755	.775
Tip to Seating Plane	L	.115	.130	.150
Lead Thickness	С	.008	.010	.015
Upper Lead Width	b1	.045	.060	.070
Lower Lead Width	b	.014	.018	.022
Overall Row Spacing §	eB	_	_	.430

#### Notes:

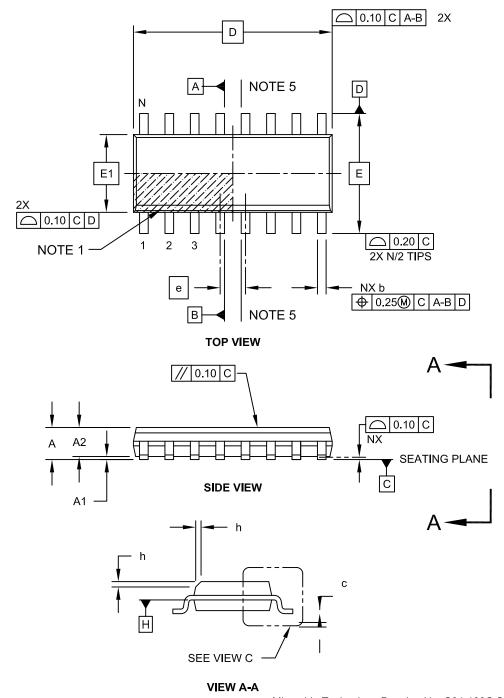
- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-017B

# 16-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

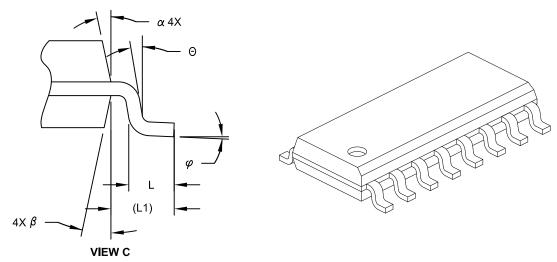
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-108C Sheet 1 of 2  $\,$ 

# 16-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units			
	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		16	
Pitch	е		1.27 BSC	
Overall Height	А	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	9.90 BSC		
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1		1.04 REF	
Lead Angle	Θ	0°	-	-
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.10	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	_	15°

#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

 ${\tt BSC: Basic\ Dimension.\ Theoretically\ exact\ value\ shown\ without\ tolerances.}$ 

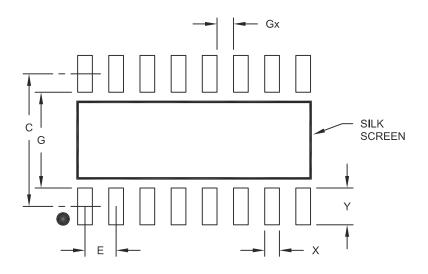
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-108C Sheet 2 of 2

# 16-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**ote:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units			S
Dimension	Dimension Limits		NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	С		5.40	
Contact Pad Width	Х			0.60
Contact Pad Length	Υ			1.50
Distance Between Pads	Gx	0.67		
Distance Between Pads	G	3.90		

#### Notes:

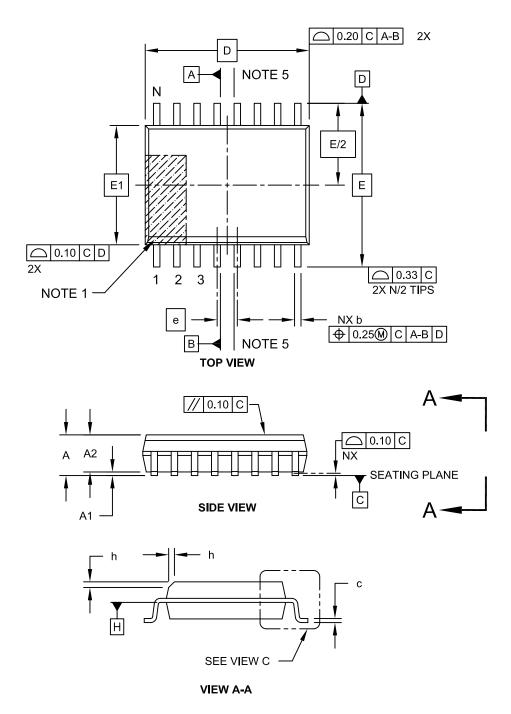
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2108A

# 16-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC]

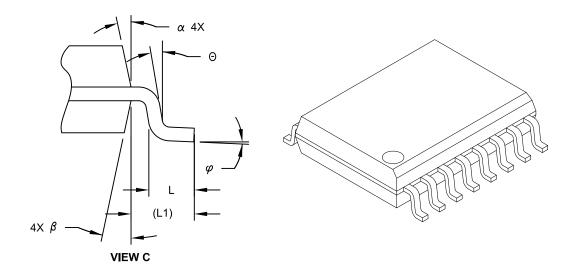
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-102C Sheet 1 of 2

# 16-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		16	
Pitch	е		1.27 BSC	
Overall Height	Α	i	-	2.65
Molded Package Thickness	A2	2.05	=	-
Standoff §	A1	0.10	-	0.30
Overall Width	Е	10.30 BSC		
Molded Package Width	E1	7.50 BSC		
Overall Length	D	•	10.30 BSC	
Chamfer (Optional)	h	0.25	-	0.75
Foot Length	L	0.40	-	1.27
Footprint	L1		1.40 REF	
Lead Angle	Θ	0°	-	=
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.20	-	0.33
Lead Width	b	0.31	_	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

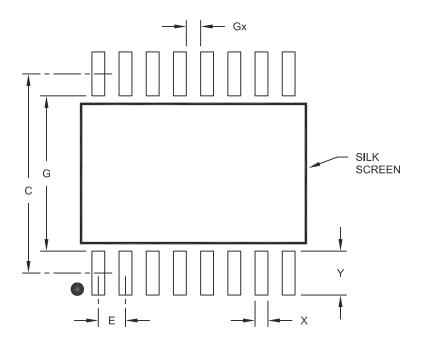
#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
  - REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-102C Sheet 2 of 2

# 16-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC] Land Pattern

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	N	<b>ILLIMETER</b>	S	
Dimension	Dimension Limits		NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	С		9.30	
Contact Pad Width	Х			0.60
Contact Pad Length	Υ			2.05
Distance Between Pads	Gx	0.67		
Distance Between Pads	G	7.25		

#### Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2102A

# APPENDIX A: REVISION HISTORY

# **Revision C (August 2012)**

The following is the list of modifications:

- 1. Re-structured the entire document.
- 2. Moved Functional Block Diagram and Typical Application figures to the front pages.
- 3. Added Temperature Characteristics table.
- Reorganized Section 2.0, Pin Description. Simplified Table 2-1, added description sections.
- 5. Added Section 4.0, Packaging Information.
- 6. Added Product Identification System section.

# **Revision B (October 2009)**

· Undocumented changes.

# Revision A (May 2009)

· Original Release of this Document.

R	F	46	C	145
$\Box$		TU		ITU

NOTES:

# PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO	. <u>/x                                      </u>	Examples:
Device	Package Number of Pins	a) RE46C145E16F: 16LD PDIP Package b) RE46C145S16F: 16LD SOIC Package c) RE46C145S16TF: 16LD SOIC Package, Tape and Reel
Device	RE46C145: CMOS Photoelectric Smoke Detector and CMOS Photoelectric Smoke Detector and Reel, SOIC only)	T L e) RE40C1455VV1b1E 1b117 SOIC Package
Package	E = Plastic Dual In-Line, 300 mil. Body, 16-Le S = Small Plastic Outline - Narrow, 3.90 mm I 16-Lead (SOIC) SW = Small Plastic Outline - Wide, 7.50 mm Bo 16-Lead (SOIC)	Bodỳ, ´

R	F	46	C	145
$\Box$		TU		ITU

NOTES:

#### Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
  knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
  Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- · Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

#### **Trademarks**

The Microchip name and logo, the Microchip logo, dsPIC, KEELOQ, KEELOQ logo, MPLAB, PIC, PICmicro, PICSTART, PIC<sup>32</sup> logo, rfPIC and UNI/O are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

FilterLab, Hampshire, HI-TECH C, Linear Active Thermistor, MXDEV, MXLAB, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, chipKIT, chipKIT logo, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, dsSPEAK, ECAN, ECONOMONITOR, FanSense, HI-TIDE, In-Circuit Serial Programming, ICSP, Mindi, MiWi, MPASM, MPLAB Certified logo, MPLIB, MPLINK, mTouch, Omniscient Code Generation, PICC, PICC-18, PICDEM, PICDEM.net, PICkit, PICtail, REAL ICE, rfLAB, Select Mode, Total Endurance, TSHARC, UniWinDriver, WiperLock and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2009-2012, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

ISBN: 978-1-62076-468-8

# QUALITY MANAGEMENT SYSTEM CERTIFIED BY DNV = ISO/TS 16949=

Microchip received ISO/TS-16949:2009 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



# **Worldwide Sales and Service**

#### **AMERICAS**

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support:

http://www.microchip.com/

support

Web Address: www.microchip.com

Atlanta

Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Boston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Cleveland

Independence, OH Tel: 216-447-0464 Fax: 216-447-0643

**Dallas** 

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Indianapolis Noblesville, IN

Tel: 317-773-8323 Fax: 317-773-5453

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara

Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto

Mississauga, Ontario,

Canada

Tel: 905-673-0699 Fax: 905-673-6509

#### ASIA/PACIFIC

**Asia Pacific Office** 

Suites 3707-14, 37th Floor Tower 6, The Gateway Harbour City, Kowloon Hong Kong

Tel: 852-2401-1200 Fax: 852-2401-3431

Australia - Sydney Tel: 61-2-9868-6733

Fax: 61-2-9868-6755

China - Beijing

Tel: 86-10-8569-7000 Fax: 86-10-8528-2104

China - Chengdu

Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Chongqing

Tel: 86-23-8980-9588 Fax: 86-23-8980-9500

China - Hangzhou

Tel: 86-571-2819-3187 Fax: 86-571-2819-3189

China - Hong Kong SAR

Tel: 852-2401-1200 Fax: 852-2401-3431

China - Nanjing

Tel: 86-25-8473-2460 Fax: 86-25-8473-2470

China - Qingdao

Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai

Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang

Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

China - Wuhan

Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian

Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

China - Xiamen

Tel: 86-592-2388138 Fax: 86-592-2388130

China - Zhuhai

Tel: 86-756-3210040 Fax: 86-756-3210049

#### ASIA/PACIFIC

India - Bangalore

Tel: 91-80-3090-4444 Fax: 91-80-3090-4123

India - New Delhi

Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune

Tel: 91-20-2566-1512 Fax: 91-20-2566-1513

Japan - Osaka

Tel: 81-66-152-7160 Fax: 81-66-152-9310

Japan - Yokohama

Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea - Daegu

Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul

Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Kuala Lumpur

Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

Malaysia - Penang

Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila

Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore

Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Hsin Chu

Tel: 886-3-5778-366 Fax: 886-3-5770-955

Taiwan - Kaohsiung

Tel: 886-7-536-4818 Fax: 886-7-330-9305

Taiwan - Taipei

Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

Thailand - Bangkok

Tel: 66-2-694-1351 Fax: 66-2-694-1350

#### **EUROPE**

Austria - Wels

Tel: 43-7242-2244-39 Fax: 43-7242-2244-393

Denmark - Copenhagen

Tel: 45-4450-2828 Fax: 45-4485-2829

France - Paris

Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

**Germany - Munich** 

Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan

Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen

Tel: 31-416-690399 Fax: 31-416-690340

**Spain - Madrid** Tel: 34-91-708-08-90

Fax: 34-91-708-08-91 **UK - Wokingham** 

Tel: 44-118-921-5869 Fax: 44-118-921-5820

11/29/11

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip: RE46C145S16TF